



Arabinda Nayak

Curriculum Vitæ (November 17, 2024)

ADDRESS

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APPOINTMENTS

2012 - Continuing	Professor of Physics Presidency University, Kolkata
2009-2012	Associate Professor of Physics Presidency College, Kolkata (2009-2010) Presidency University, Kolkata (2010-2012)
2006-2009	Reader in Physics Presidency College, Kolkata
2002-2006	Lecturer (Sr. Scale) in Physics Presidency College, Kolkata
1997-2002	Lecturer in Physics Darjeeling Govt. College, Darjeeling
1996-1997	Lecturer in Physics North Eastern Regional Institute of Science & Technology, AP
1993-1996	Postdoctoral Fellow (RA, CSIR) Material Science Center, IIT Kharagpur

[Research on the Preparation and
Characterization of Diamond and
Diamond-Like-Carbon \(DLC\) Films](#)

MAJOR ADMINISTRATIVE RESPONSIBILITIES

2019-2024	Director, Internal Quality Assurance Cell (IQAC) Presidency University, Kolkata
2017-2022	Nodal Officer, Undergraduate & Postgraduate Admissions, Presidency University, Kolkata
2016-2019	Dean of Faculty of Natural and Mathematical Sciences Presidency University, Kolkata
2016-2023	Professor-in-Charge, Presidency University Library Services, Presidency University, Kolkata
2002-2004	Assistant Superintendent (Govt. Eden Hindu Hostel)
2001-2002	Head of the Department of Physics, Darjeeling Govt. College

EDUCATION

1988-1993	PhD Materials Science, Materials Science Center, IIT, Kharagpur "Studies on Structural, Electrical and Optical Properties of Electron Beam Deposited Zn_3P_2 - Cd_3P_2 Thin Films" Thesis advisors: Professor D.R. Rao and Professor H.D. Banerjee
1982-1987	MSc Physics (5-year Integrated) Department of Physics, IIT, Kharagpur

NATIONAL ELIGIBILITY TEST STATUS

- Joint CSIR - UGC NET (1988)
- GATE (1988)

SOCIETY MEMBERSHIP

- Life member, Indian Association for the Cultivation of Science, Kolkata
- Life Member, Materials Research Society of India (MRSI)

FIELD OF SPECILZATION

- Experimental Condensed Matter Physics & Materials Science

MAJOR RESEARCH INTEREST

- Synthesis and Evaluation of Semiconductor Thin Films
- Growth and Realization of Ferroelectric Materials/Films for Solar Cell and Photodetector Applications.
- Development of Ge And ZnO-Based Nanomaterials
- Diamond &Diamond-Like-Carbon Films
- Polymer-Inorganic Hybrid Nanocomposites
- Development of Zinc-Tin-Phosphide Based Chalcopyrite Thin Films for Solar Cell Application
- Photodetectors &Multi-Junction Solar Cells
- Computational Materials Science &Optical Response of Functional Materials

PEER-REVIEWED JOURNAL PAPERS

1. **Nayak, A.**, Rao, D.R., and Banerjee, H.D. Optical Studies on Electron Beam Deposited Zn₃P₂ Thin Films. *J. Mater. Sci. Lett.* Vol.10, P.403-405 (1991). DOI: 10.1007/ BF00728046
2. **Nayak, A.**, Rao, D.R., and Banerjee, H.D. Electrical and Optical Properties of e-Beam Evaporated Zn₃P₂ Thin Films. *Bull. Electrochem.* Vol.7, P. 133 - 135 (1991).

3. **Nayak, A.**, Rao, D.R., and Banerjee, H.D. Derivative Spectra of Polycrystalline Zn_3P_2 Thin Films. *Solid State Comm.* Vol. **78**, P. 149-151 (1991). DOI: 10.1016/0038-1098(91)90272-W
4. Rao, D.R., **Nayak, A.** Preparation and Characterization of Zn_3P_2 - Cd_3P_2 Solid Solutions. *J. Mater. Sci.* Vol. **27**, P. 4389-4392 (1992). DOI: 10.1007/BF00541571
5. **Nayak, A.** and Rao, D.R. Optical Constant of Zn_3P_2 - Cd_3P_2 Thin Films. *Optical Materials*. Vol. **1**, P. 85-89 (1992). DOI: 0.1016/0925-3467(92)90005-8
6. Rao, D.R., **Nayak, A.** Preparation and Characterization of Cd_3P_2 Thin Films. *J. Appl. Phys.* Vol. **74**, P. 214 - 218 (1993). DOI: 10.1063/1.354148.
7. **Nayak, A.** and Rao, D.R. Photoluminescence Spectra of Zn_3P_2 - Cd_3P_2 Alloy Films. *Appl. Phys. Lett.* Vol. **63**, P. 592-593 (1993). DOI: 10.1063/1.110779.
8. **Nayak, A.** and Rao, D.R. Electrical Properties of Electron Beam Evaporated Zn_3P_2 - Cd_3P_2 Alloy Films. *Matter. Chem. & Phys.* Vol. **37**, P. 225-229 (1994).
9. **Nayak, A.** and Banerjee, H.D. Bonding Characteristics and Optical Properties of Amorphous Carbon/Diamond Films Deposited by Electron Beam Activated Plasma CVD Method. *Phys. Stat. Sol (a)*. Vol. **149**, P. 629-635 (1995). DOI: 10.1002/pssa.2211490213.
10. **Nayak, A.** and Banerjee, H.D. Electron Beam Activated Plasma Chemical Vapour Deposition of Polycrystalline Diamond Films. *Phys. Stat. Sol (a)*. Vol. **151**, P. 107-111 (1995). DOI: 10.1002/pssa.2211510112.
11. **Nayak, A.** and Banerjee, H.D. Bonding and Optical Properties of Diamond Like Hydrocarbon Films Deposited by Plasma Decomposition of Acetylene: The Role of Water Vapour Addition. *Mater. Chem. & Phys.* Vol. **47**, P. 159 - 163 (1997). DOI: 10.1016/S0254-0584(97)80045-4.
12. **Nayak, A.** and Banerjee, H.D. Photoluminescence Spectroscopic Investigation on the Quality of Diamond Films Grown in Oxy-Acetylene Combustion Flame. *Thin Solid Films*. Vol. **298**, P. 14-21 (1997). DOI: 10.1016/S0040-6090(96)09139-0.
13. **Nayak, A.** and Banerjee, H.D. X-Ray Photoelectron Spectroscopy of Zinc Phosphide Thin Films. *Appl. Surf. Sci.* Vol. **148**, P. 205-210 (1999). DOI: 10.1016/S0169-4332(99)00144-0.

14. **Nayak, A.** and Banerjee, H.D. X-Ray Photoelectron Spectra of Zn₃P₂-Cd₃P₂ Alloy Semiconducting Thin Films. *Matter. Chem & Phys*. Vol. **60**, P. 95-98 (1999).
15. Halder, S.R., **Nayak, A.**, Chini, Roy, S.K., Yamamoto, N. and Bhunia, S. Vapor condensation growth and evaluation mechanism of ZnO nanorod flower structures. *Phys. Stat. Sol. (a)*. Vol. **207**, P.364-369 (2009). DOI: 10.1002/pssa.200925223.
16. Halder, S.R., **Nayak, A.**, Chini, T.K. and Bhunia, S. Strong temperature and substrate effect on ZnO nanorod flower structures in modified chemical vapor condensation growth. *Current Appl. Phys.* Vol. **10**, P.942-946 (2010). DOI:10.1016/j.cap.2009.11.077.
17. Haldar, I., Kundu, A., Biswas, M., and **Nayak, A.** Preparation and evaluation of a poly (N-vinylcarbazole)-Fe₃O₄ (PNVC-Fe₃O₄) nanocomposite. *Matter. Chem & Phys*. Vol. **128**, P. 256-264 (2011). DOI: 10.1016/j.matchemphys.2011.03.008.
18. Haldar, I., Biswas, M., and **Nayak, A.** Microstructure, dielectric response and electrical properties of polypyrrole modified poly (N-vinylcarbazole) - Fe₃O₄ (PNVC - Fe₃O₄) nanocomposites. *Synthetic Metals*. Vol. **161**, P. 1400-1407 (2011). DOI: 10.1016/j.synthmet. 2011.05.008.
19. Haldar, I., Biswas, M., and **Nayak, A.** Preparation and evaluation of microstructure, dielectric and conductivity (ac/dc) characteristics of a polyaniline/ poly N-vinylcarbazole/ Fe₃O₄ nanocomposites. *J. Polym. Res.* Vol. **19**, P. 9951:1-9 (2012). DOI: 10.1007/s10965-012-9951-0.
20. Haldar, I., Biswas, M., **Nayak, A.** and Sinha Ray, S. Morphological, dielectric and electrical conductivity characteristics of clay-containing nanohybrids of poly (N-vinylcarbazole) and polypyrrole. *J. Nanosci. Nanotech.* Vol. **12**, P. 7841-7848 (2012). DOI: 10.1166/jnn.2012.6589.
21. Haldar, I., Biswas, M., **Nayak, A.** and Sinha Ray, S. Dielectric Properties of Polyaniline-Montmorillonite Clay Hybrids. *J. Nanosci. Nanotech.* Vol. **13 (1-6)**, P. 1824-1829 (2013). DOI: 10.1166/jnn.2013.7125.
22. **Nayak, A.** and Bhunia, S. Microstructure and dielectric functions of Ge nanocrystals embedded between amorphous Al₂O₃ films: study of confinement and disorder. *J. Exptl. Nanosci.* Vol. **9**, **463-474** (2014). DOI:10.1080/17458080.2012.669852.
23. Haldar, I., Biswas, M., and **Nayak, A.** Dielectric and Conductivity Characteristics of CuCl₂ Doped Poly (N-vinyl

- carbazole) and Its Hybrid Nanocomposites with Fe₃O₄. *J.Nanosci. Nanotech.* Vol. 14 (N.8), P. 5774-5778 (2014). DOI: 10.1166/jnn.2014.8885.
24. Haldar, I., Biswas, M., and **Nayak, A.** Some Observations on the Dielectric and Conductivity Behavior of Nanocomposites of Polyaniline with Fe₃O₄ and CuFe₂O₄. *Polymer-Plastics Technol. & Engg.* Vol. 53, P. 1317-1326 (2014). DOI: 10.1080/03602559.2014.886118.
25. Sarkar, S.K., Raul, K.K., Pradhan, S.S., Basu, S., **Nayak, A.** Magnetic Properties of Graphite Oxide and Reduced Graphene Oxide. *Physica E: Low-dimensional Systems and Nanostructure.* Vol. 64, P. 78-82 (2014). DOI: 10.1016/j.physe.2014.07.014.
26. Samanta, S., Jana, K., Gupta, K., **Nayak, A.**, Ghosh, U.C. NiV₂O₆-incorporated poly-(3, 4-ethylenedioxythiophene) polymer nanocomposite: synthesis, characterization, temperature dependent dielectric property and ac-conductivity relaxation behavior. *Mater. Chem. Phys.* Vol. 182, 173-181(2016). DOI: 10.1016/j.matchemphys.2016.07.020.
27. Das, R., Gupta, K., Jana, K., **Nayak, A.**, Ghosh, U.C. Preparation, characterization and dielectric, ac conductivity with electrochemical behavior of strontium zirconate. *Adv. Mater. Lett.* Vol. 7(8), P. 646-651(2016). DOI: 10.5185/amlett.2016.6294.
28. Haldar, I., **Nayak, A.** Dielectric, ac conductivity relaxation and magnetoresistive behaviors of BaTiO₃-ppy nanocomposites. *J. Nanosci. Nanotech.* Vol. 17, P. 4658-4666(2017). DOI: 10.1166/jnn.2017.13784.
29. Mukherjee, S., Pradhan, A., Maitra, T., Mukherjee, S., **Nayak, A.**, Bhunia, S. Phase selective growth of Ge nanocrystalline films by ionized cluster beam deposition technique and photo-oxidation study. *Adv. Mater. Lett.* Vol. 8(9), P. 891-896 (2017). DOI: 10.5185/amlett.2017.1462.
30. Maitra, T., Mukherjee, S., **Nayak, A.**, Pradhan, A., Mukherjee, S., Bhunia, S. Temperature and Excitation Dependent Lasing Characteristics of ZnO Nanorods. *Invertis Journal of Science & Technology.* Vol. 10(3), P. 148-151 (2017). DOI: 10.5958/2454-762X.2017.00023.3
31. Mukherjee, S., Maitra, T., **Nayak, A.**, Pradhan, A., Mukherjee, S., Bhunia, S. Interface characteristics of ZnSnP₂/Si heterostructure studied by x-ray reflectivity measurement. *Invertis Journal of Science & Technology.* Vol. 10(3), P. 137-141 (2017). DOI: 10.5958/2454-762X.2017.00021.X.

32. Sadhukhan, B., Nayak, A., Mookherjee, A. Effect of Doping on the Electronic Properties of Graphene and T-graphene: A Theoretical Approach. *Ind. J. Phys.* Vol. **91**, Issue **12**, P. 1541-1552 (2017); DOI: 10.1007/s12648-017-1067-2.
33. Sadhukhan, B., Bandyopadhyay, S., **Nayak, A.**, Mookherjee, A. Disorder Induced Lifetime Effects in Binary Disordered Systems: A First Principles Formalism and an Application to Doped Graphene. *Int. J. Mod. Phys. B.* Vol.**31**, P. 1750218-1750232(2017); DOI: 10.1142/S0217979217502186.
34. Sadhukhan, B., Singh, P., **Nayak, A.**, Datta, S., Johnson, D.D., Mookherjee, A. Band-gap Tuning and Optical Response of Two-dimensional $\text{Si}_x\text{C}_{1-x}$: A First-principles Real Space Study of Disordered 2D Materials. *Phys. Rev. B.* **96**, 054203 (2017).
35. Sadhukhan, B., **Nayak, A.**, Mookherjee, A. Effect of Disorder on the Optical Response of NiPt and Ni_3Pt Alloys. *Computational Mater. Sci.* Vol. **140**, 1-9 (2017). DOI:10.1016/j.commatsci.2017.08.003.
36. Mukherjee, S., Maitra, T., **Nayak, A.**, Mukherjee, S., Pradhan, A., Mukhopadhyay, M.K., Satpati, B., Bhunia, S. Microstructural and light emission properties of ZnSnP_2 thin film absorber: study of native defects. *Mater. Chem. Phys.*, Vol.**204**, 147-153, (2018). DOI: 10.1016/j.matchemphys.2017.10.014
37. Pradhan, A., Maitra, T., Mukherjee, S., Mukherjee, S., **Nayak, A.**, Satpati, B., Bhunia, S. Spontaneous superlattice structures in $\text{Al}_x\text{Ga}_{1-x}\text{As}$ / GaAs (100) grown by metalorganic vapor phase epitaxy. *Materials Letts.* Vol. **210**, P. 77-79 (2018). DOI: 10.1016/j.matlet.2017.08.133.
38. Maitra, T., Pradhan, A., Mukherjee, S., Mukherjee, S., **Nayak, A.**, Bhunia, S. Evaluation of spontaneous superlattice ordering in MOCVD grown $\text{Al}_x\text{Ga}_{1-x}\text{As}$ epilayer on GaAs (100) using X-ray reflectivity and rocking curve analysis. *Physica E: Low-dimensional Systems and Nanostructures.* Vol. **106**, P. 357-362 (2018). DOI: 10.1016/j.physe.2018.03.020.
39. Mukherjee, S., Maitra, T., Pradhan, A., Mukherjee, S., Manna, G., Bhunia, S., **Nayak, A.** Fast responsive $\text{Mg}/\text{ZnSnP}_2/\text{Sn}$ photodetector for visible to near-infrared application. *Solar Energy Materials and Solar Cells.* Vol. **189**, P. 181-187 (2019). DOI: 10.1016/j.solmat.2018.09.034.
40. *Mukherjee, S., Pradhan, A., Mukherjee, S., Maitra, T., Sengupta, S., Satpati, B., Chakrabarti, S., **Nayak, A.**, Bhunia, S. Tuning of near infrared excitonic emission from InAs quantum dots by controlling the sub-*

monolayer coverage. J. Luminescence. Vol. 210, P. 311-321 (2019). DOI: 10.1016/j.jlumin. 2019.01.063.

41. Pradhan, A., Mukherjee, S., Maitra, T., Mukherjee, S., **Nayak, A.**, Bhunia, S. Interface intermixing and interdiffusion characteristics in MOVPE grown spontaneous Al_xGa_{1-x}As/GaAs (100) superlattice structures using high resolution X-ray diffraction. *Superlattice and Microstructure*. Vol. 126, P. 193-199 (2019). DOI: 10.1016/j.spmi.2019.01.001.
42. Maitra, T., Pradhan, A., Mukherjee, S., Mukherjee, S., **Nayak, A.**, Bhunia, S. Temperature and excitation dependent ultraviolet lasing in vertically oriented ZnO nanowires. *J. Mater. Sci.: Materials for Electronics*. Vol. 30, P. 8814-8819 (2019). DOI: 10.1007/s10854-019-01206-2.
43. Mukherjee, S., A. Pradhan, A., Mukherjee, S., Maitra, T., Sengupta, S., Chakrabarti, S., **Nayak, A.**, Bhunia, S. Carrier escape mechanism in laterally correlated InAs sub-monolayer quantum dots using temperature dependent photoluminescence. *J. Luminescence*. Vol. 215, P. 116597 (2019). DOI: 10.1016/j.jlumin.2019.116597.
44. Pradhan, A., Mukherjee, S., Maitra, T., Mukherjee, S., **Nayak, A.**, Bhunia, S. Improved spectral and temporal response of MSM photodetectors fabricated on MOCVD grown spontaneous AlGaAs superlattice. *Sensors and Actuators A: Physical*. Vol. 297, P. 111548 (2019). DOI: 10.1016/j.sna.2019.111548.
45. Mukherjee, S., Maitra, T., Pradhan, A., Mukherjee, S., Bhunia, S., **Nayak, A.** Probing bias and power dependency of high-performance broadband Mg/ZnSnP₂/Sn back-to-back Schottky junction photodetectors. *Solar Energy Materials and Solar Cells*. Vol. 208, P. 110386 (2020). DOI: 10.1016/j.solmat.2019.110386.
46. Maitra, T., Mukherjee, S., Pradhan, A., Mukherjee, S., **Nayak, A.**, Bhunia, S. Fast-response symmetric coplanar Ni/AlGaInP/Ni visible photodetector. *Sensors and Actuators A: Physical*. Vol. 305, P. 111933 (2020). DOI: 10.1016/j.sna.2020.111933.
47. Maitra, T., Pradhan, A., Mukherjee, S., Mukherjee, S., **Nayak, A.**, Bhunia, S. Spectral and temporal performance enhancement in a symmetric co-planar Au-Ge/AlGaAs/Au-Ge natural superlattice-based MSM photodetector. *J. Mater. Sci.: Materials for Electronics*. Vol. 33, P. 9690-96999 (2022). DOI: 10.1007/s10854-022-07720-0.

48. Mohsin, Md., Bhunia, S., Nayak, A. Ferroelectric ZnSnS₃ thin films: growth and measurement of photovoltaic properties. *J Mater Sci: Materials for Electronics*. Vol. **34**, 2194(2023). DOI: 10.1007/s10854-023-11545-w.
49. Pradhan, A., Maitra, T., Mukherjee, S., Mukherjee, S., **Nayak, A.**, Bhunia, S. Effect of spontaneous superlattice ordering on the luminescence properties of the MOVPE grown AlGaAs/GaAs (100) heterostructures. *Optical Materials*. Vol. **150**, 115156 (2024). DOI: 10.1016/j.optmat.2024.115156.
50. Mohsin, Md., Sharma, J., Ghorai, G., Sahoo, P. K., Bhunia, S., Nayak, A. Characterization of polycrystalline bulk ferroelectric ZnSnS₃ synthesized by hydrothermal method for photovoltaic application. *Materials Today Communications*. Vol. **41**, 110387 (2024). DOI: 10.1016/j.mtcomm.2024.110387.

PAPER PUBLISHED IN CONFERENCE

PROCEEDINGS

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1. Mukherjee, S., Pradhan, A., Mukherjee S., Maitra, T., **Nayak, A.**, Bhunia, S. (2016) Growth and Characterization of Cubic and Non-Cubic Ge Nanocrystals. *AIP Conf. Proc.* Vol. **1728**, P. 0220111-1-020111-5; DOI: 10.1063/1.4946162.
 2. Pradhan, A., Maitra, T., Mukherjee, S., Mukherjee S., **Nayak, A.**, Satpati, B., Bhunia, S. (2016) Observation of Natural Superlattice in Al_xGa_{1-x}As Layers Grown by Metalorganic Vapour Phase Epitaxy. *AIP Conf. Proc.* Vol. **1728**, P. 020243-1-020243-6; DOI:10.1063/1.4946294.
 3. Mukherjee, S., Pradhan, A., Mukherjee, S., Maitra, T., Sengupta, S., Chakrabarti, S., **Nayak, A.**, Bhunia, S. (2018) Growth and characterization of InAs sub-monolayer quantum dots with varying fractional coverage. *AIP Conf. Proc.* 1942, 080039. DOI:10.1063/1.5028873.
 4. Pradhan, A., Maitra, T., Mukherjee, S., Mukherjee, S., Satpati, B., **Nayak, A.**, Bhunia, S. (2018) Study of thermal stability of spontaneously grown superlattice structures by metalorganic vapor phase epitaxy in Al_x Ga_{1-x} As/ GaAs heterostructure. *AIP Conf. Proc.* 1942, 080038. DOI: 10.1063/1.5028872.

**PAPER PRESENTED IN SEMINARS AND
CONFERENCES (2006 - 2023)**

5. **Nayak, A.**, Bhunia, S. and Chini, T.K. (2006) Growth of flower-like ZnO nanocrystals at low temperature. [International Conference on Lasers and Nanomaterials \(ICLAN\)](#); held at Saha Institute of Nuclear Physics Campus, Kolkata. November 10 - December, 2006.
6. **Nayak, A.** and Chetri, R. (2008) Microstructure and optical studies of non-cubic germanium nanocrystals. [Condensed Matter Days-2008](#); held at Department of Physics, Visva-Bharati, India. August 29-31, 2008.
7. **Nayak, A.**, Haldar, I and Biswas, M. (2012) Microstructure, dielectric and conductivity characteristics of polypyrrole and polyaniline modified (poly-N-vinyl carbazole-Fe₃O₄) nanocomposites. [International Conference on Nanoscience and Technology \(ICONSAT 2012\)](#), ARCI, Hyderabad, India. 20 - 23 January, 2012.
8. **Mukherjee, S., Maitra, T., Pradhan, A., Mukherjee, S., Nayak, A., Bhunia, S.** Growth and Characterization of AlAs/GaAs Distributed Bragg Reflector structure by Metal Organic Chemical Vapor Deposition. [National Conference on Nanotechnology: Materials and Applications \(NCoN:M&A\), Organized by School of materials science and Nanotechnology, Jadavpur University, Venue: Jadavpur University, West Bengal. Date: 16th-17th June 2016.](#)
9. **Mukherjee, S., Maitra, T., Nayak, A., Pradhan, A., Mukherjee, S., Bhunia, S.** Interface characteristics of ZnSnP₂/Si heterostructure studied by x-ray reflectivity measurement. [ISSMD 4 Symposium, Organized by School of materials science and Nanotechnology, Jadavpur University, Venue: Jadavpur University, West Bengal. Date: 8th-10th March 2017.](#)
10. **Maitra, T., Pradhan, A., Mukherjee, S., Mukherjee, S., Nayak, A., Bhunia, S.** Metal Organic Chemical Vapor Deposition growth and characterization of (Al_yGa_{1-y})_xIn_(1-x)P/GaAs semiconductor heterostructures. [National Conference on Nanotechnology: Materials and Applications \(NCoN:M&A\), Organized by School of materials science and Nanotechnology, Jadavpur University,](#)

Venue: Jadavpur University, West Bengal. **Date:** 16th-17th June 2016.

11. **Maitra, T., Pradhan, A., Mukherjee, S., Mukherjee, S., Nayak, A., Bhunia, S.** Temperature and Excitation Dependent Lasing Characteristics of ZnO Nanorods. [ISSMD 4 Symposium, Organized by School of materials science and Nanotechnology, Jadavpur University](#), **Venue:** Jadavpur University, West Bengal. **Date:** 8th-10th March 2017.
12. **Mukherjee, S., Maitra, T., Pradhan, A., Mukherjee, S., Bhunia, S., Nayak, A.** A Novel Lead-free ZnSnP₂ semiconductor thin film for solar cell and self-powered photodetection, [NCFMP 2018 Organized by Adamas University](#), **Venue:** Barasat, West Bengal. August 16-17, 2018.
13. **Mukherjee, S., Maitra, T., Pradhan, A., Mukherjee, S., Nayak, A., Bhunia, S.** Fast visible-NIR metal-semiconductor-metal photodetector using KBiFe₂O₅, [IWPSD 2019, XXth International Workshop on Physics of Semiconductor Devices: IWPSD 2019](#), **Venue:** Novotel Hotel and Residences, Kolkata, India. December 17-20, 2019.
14. **Maitra, T., Mukherjee, S., Rahman, M., Pradhan, A., Mukherjee, S., Nayak, A., Bhunia, S.** Investigation of Structural, Optical, and Multiferroic properties of Chromium Doped Nanocrystalline GdFeO₃, [NCFMP 2018 Organized by Adamas University](#), **Venue:** Barasat, West Bengal. August 16-17, 2018.

15. **Maitra, T., Pradhan, A., Mukherjee, S., Mukherjee, S., Nayak, A., Bhunia, S.** Probing Interface roughness of the GaAs/Al_{0.3}Ga_{0.7}As Multi-quantum-well Structures Using Low-temperature Photoluminescence Spectra, [3rd International Conference on Condensed Matter and Applied Physics. \(ICC-2019\)](#), organized by Govt. Engineering College Bikaner & Ceramic Electrical Research & Development Centre, **Venue:** Bikaner, Rajasthan. **Date:** October 14-15, 2019.
16. **Maitra, T., Mukherjee, S., Pradhan, A., Mukherjee, S., Nayak, A., Bhunia, S.** Visible-NIR photodetector based on Au-Ge/(Al_yGa_{1-y})_xIn_{1-x}P/Ni asymmetric coplanar metal-semiconductor-metal structure, [IWPSD 2019, XXth International Workshop on Physics of Semiconductor Devices: IWPSD 2019](#), **Venue:** Novotel Hotel and Residences, Kolkata, India. **Date:** December 17-20, 2019.
17. **Mohsin, Md., Bhunia, S., Nayak, A.** Microstructural and optical properties of ferroelectric ZnSnS₃ films grown by spray

pyrolysis method (Poster Presentation), [International conference on advance physics \(IEMPHYS-22\)](#), Organised (Online mode) by IEM, Institute of Engineering and Management, Kolkata. Date: 22-24 September, 2022.

18. **Mohsin, Md.**, Ghose, I., Bhunia, S., **Nayak, A.**, Electrical behaviors of ferroelectric ZnSnS₃ thin films synthesized by spray pyrolysis method for photovoltaic applications, [7th International conference on Nanoscience and Nanotechnology \(ICONN-23\)](#). Organised by (virtual)- SRM Institute of Science and Technology. Date: 27-29 March, 2023.

MY RESEARCH LABORATORY

- I have set up one Solid State and Materials Science research laboratory for the deposition and evaluation of ultra-fine (down to 5 nm) germanium (Ge) particles, ZnO nanocrystals, thin film and crystalline compound semiconductors and conducting polymer-inorganic hybrid nanocomposites for device applications. The equipped with an Ionized Cluster Beam (ICB) deposition system for the growth of Ge nanoparticles ([funded by DST, Govt. of India](#)). Recently, one Bridgman growth apparatus has been installed for the growth of ZnSnP₂ single crystal ([funded by UGC](#)).
- An experimental set up for the measurement of ac conductivity and dielectric response for the nanocomposite materials at elevated temperatures has also been designed by me and fabricated under the [FRPDF grant](#) provided by the Presidency University.
- The laboratory also equipped with supporting instruments for material preparation such as Centrifuge (up to 5000 rpm), Spin Coating system, UV light source (200 W), magnetic stirrer with hot plate etc. ([purchased from FRPDF grant](#)).
- The laboratory is recently equipped with an Spray Pyrolysis deposition system for the growth of ZnSnS₃ thin films at elevated temperatures ([funded by SERB-DST, Govt. of India](#)).

SUPERVISING OF RESEARCH SCHOLARS FOR Ph.D DEGREE

1. **Tamaghna Maitra (NET, UGC)**. [Research Proposal: Metalorganic Vapor Phase Epitaxial \(MOVPE\) growth of Ge/In_xGa_{1-x}P multi quantum wells \(Awarded, 2021\)](#).
2. **Sukhendu Mukherjee (NET, UGC Project)**. [Research Proposal: Development, Synthesis and Characterization of ZnSnP₂](#)

Chalcopyrite Thin Film for Photovoltaic Devices (Awarded 2020).

3. **BanasreeSadhukhan.** Research Proposal: Optical conductivity and dielectric function of NiPt alloy systems. (Awarded, 2019).
4. **Md.Mohsin.** Research Proposal: Growth and realization of ferroelectric-photovoltaic effect in ZnSnS₃ thin films for solar cell and photodetector applications.

SUPERVISION OF JRF/SRF

- **Ipsita Halder (SRF, CSIR, 2015-2015).** **Research:Dielectric, ac conductivity relaxation and magnetoresistive behaviors of BaTiO₃-ppy nanocomposites**

Research Finding: Nano crystalline BaTiO₃ and polypyrrole (ppy)-BaTiO₃ hybrid nanocomposites have been synthesized using chemical oxidative polymerization method. Microstructure and crystallinity of the hybrids are studied using field emission scanning electron microscope (FE-SEM), high resolution transmission electron microscope (HRTEM) and X-ray diffraction (XRD) technique. As prepared BaTiO₃ are rod-like, while PPY-BaTiO₃ nanocomposites indicate the formation of bulging agglomerates of spherical particles with various sizes (40-50 nm). Dielectric constants at room temperature of the composites have largely enhanced (up to 6000). The hybrid composite shows grain boundary relaxation in the frequency range (42 Hz-5 MHz). Three dimensional (3D) variable range hopping (VRH) with high localization of charge carriers (Mott temperature ≈ 8725658 K) is observed in the temperature dependent conductivity evaluation of composite system. Negative magnetoresistance (MR $\approx 4.3\%$) has been measured at 1 T. The observed MR is explained with the help of forward interference model.

MAJOR RESEARCH PROJECT (COMPLETED)

- **Development of Tetragonal Ge-nanocrystals by Ionized Cluster Beam Deposition Technique: A New Light Emitting Materials for Future Optoelectronic.**

Sponsoring Authority: DST, Govt. of India. D.D.No.SR/ S2/ CMP - 53/ 2003.

Amount: 24 Lakh. Duration: 11/10/2006 to 10/10/2009.

Research Finding: We have successfully deposited Ge-NCs on Si (100) and quartz substrates by ICB deposition technique

developed in our laboratory. Ge nanocrystals mostly with tetragonal phase were obtained when grown using neutral cluster. A composite phase containing both tetragonal and high percentage of diamond cubic structure of Ge-NCs could be grown when the clusters were ionized and subsequently accelerated with potential greater than 1.50 kV. HRTEM techniques were used to study the microstructure of the crystallites. Optical band gap of the Ge-films were in the range 1.55 eV-1.60 eV. The UV light illumination has a pronounced effect on the optical spectra of the non-cubic Ge-NCs.

Germanium nanocrystals embedded between amorphous Al₂O₃ layers deposited by ICB deposition technique exhibited distinct microcrystalline structures with progressively lowering of disorder with thermal treatment. Such NCs are promising for the non-volatile memory devices.

- **Polymer-Inorganic Hybrid Nanocomposites: Preparation, Characterization and their Potential as Nanodielectrics.**

Sponsoring Authority: CSIR, New Delhi. Sanction No: CSIR-01(2342)/09/EMR-II.

Amount: 13.68 Lakh. Duration: from 01.11.2009 to 31.10.2013. (In collaboration with Department of Chemistry).

Research Finding: A nanocomposite of PNVC and nano-dimensional Fe₃O₄ (PNVC-Fe₃O₄) was prepared by insitu solid state polymerization of N-vinylcarbazole by Fe₃O₄ at 65°C. PPY encapsulated PNVC-Fe₃O₄ nanocomposite was synthesized via polymerization of PY in an aqueous suspension of PNVC-Fe₃O₄ composite in presence of KPS. The formations of PNVC and of PPY in the PPY-(PNVC-Fe₃O₄) system were confirmed by FTIR analysis. TGA and DTA analyses showed the thermal stability trend as Fe₃O₄ > PNVC-Fe₃O₄ > PPY-(PNVC-Fe₃O₄) > PNVC. HRTEM studies revealed that the PPY-(PNVC-Fe₃O₄) nanoparticles have an average grain size of 37 nm with the Fe₃O₄ nanoparticles fairly well-dispersed in the composite matrix. The SEM study showed a spherical morphology of PPY-(PNVC-Fe₃O₄) particles. XRD studies also confirmed the particle size to be 37 nm. The dielectric constants of PNVC-Fe₃O₄ and the PPY-Fe₃O₄ systems (110-400) were improved relative to the base polymers. In contrast, the PPY encapsulated PNVC-Fe₃O₄ nanocomposites showed significantly higher values of dielectric constant (>1000). The interfaces between polymer and oxide layers play crucial roles for enhancing dielectric properties of the system. The ac

conductivity was found to be independent of frequency in the range 10^2 to 10^3 Hz for all the nanocomposites and rise thereafter appreciably in the frequency range of 1 kHz to 25 kHz.

- **Development, Synthesis and Characterization of ZnSnP₂ Chalcopyrite Thin Film for Photovoltaic Devices.**

Sponsoring Authority: UGC, New Delhi. Sanction No.MRP-MAJOR-MATE-2013-16190.

Amount: 11.91 Lakh. Duration: from 01.07.2015 to 31.06.2018.

ZnSnP₂, a member of II-IV-V₂ group compound semiconductors, has recently attracted much attention as a potential absorbing material for thin film solar cell applications. Recent theoretical calculations on the electronic structure of ZnSnP₂ indicate that it possesses an order chalcopyrite structure which can transform to a disordered sphalerite structure at high temperature (720°C) with a variation of room temperature optical band gaps from 1.70 eV to 0.75 eV. In the chalcopyrite structure (bandgap = 1.70 eV), Zn and Sn occupy on specific sites of the fcc lattice, while in the sphalerite structure (bandgap = 0.75 eV) they are randomly distributed on fcc sites giving rise to disorder phase. This feature indicates that bandgap of ZnSnP₂ could be tuned from 0.75 eV to 1.70 eV by controlling growth temperature and hence the atomic configuration. The grading of band gaps from low to high values could be achieved by growing an initial layer at a higher temperature corresponding to lower band gap and then the subsequent layers are grown at relatively lower temperatures. The exact growth temperatures and their relation to the band gap values of ZnSnP₂ need to be optimized properly. Thus, the band gap tuning facilitates the fabrication of various homo p-n junctions by properly choosing a definite phase of ZnSnP₂ and doping. Interestingly, an optical band gap of 1.68 eV, which is close to the optimum band gap (~ 1.50 eV) at the Shockley-Quisser limit, has been reported. Moreover, other advantages such as ternary ZnSnP₂ is low-toxic, the constituent elements for the preparation of ZnSnP₂ are earth abundant and inexpensive and high absorption coefficient ($> 10^4$ cm⁻¹) above 1.60 eV, find ZnSnP₂ a potential alternative for photovoltaic device applications. It has excellent lattice matching with GaAs substrates. The growth of ZnSnP₂ thin films have been reported previously by co-evaporation and in ultrahigh vacuum by molecular beam epitaxy (MBE). Recently, ZnSnP₂ based thin-film solar cell with ZnSnP₂ absorber is fabricated by

phosphidation method under the variation of Zn/Sn atomic ratio. The solar cell parameters ($J_{sc} = 2.63 \text{ mA/cm}^2$, $V_{oc} = 3.7 \text{ mV}$, $FF = 27.2\%$, and conversion efficiency = 0.0027%) have been measured using near-stoichiometric ZnSnP_2 as the absorber layer. In the study, the authors found two different current areas. Low-current area is attributed to the presence of Zn_3P_2 secondary phase forming the shunt paths while the high-current area (0.014 cm^2) with efficiency = 0.021%, $J_{sc} = 5.03 \text{ mA/cm}^2$ is obtained due to the formation of pure ZnSnP_2 phase. The energy band gap of ZnSnP_2 thin film prepared by phosphidation method was reported as 1.38 eV indicating the growth of sphalerite ZnSnP_2 structure with appropriate variation of Zn/Sn atomic ratio. In few cases, J-V characteristics of the hetero-junction solar cell [Al/AZO/ ZnO/CdS/ ZnSnP_2 /Mo] have been studied. The performance of the fabricated cell was found quite low (conversion efficiency is 0.087%). Necessary modifications of the cell structure to achieve better performances such as improvement of the resistance of the hetero-interfaces and the use of appropriate buffer materials have been suggested.

Though some limited studies have been made by several researchers on the preparation of crystalline bulk material and thin epitaxial layer, detailed understanding of optical and electrical properties, the nature of native defects responsible for top-type conductivity in ZnSnP_2 are still obscure. In ZnSnP_2 thin film, zinc vacancies or zinc-on-tin sites are considered as acceptor which is responsible for p-type conductivity. Defects introduce localized levels in the energy gap of ZnSnP_2 and other compound semiconductors through which they control solar cell device performance, efficiency and reliability. Native defects such as vacancies, self-interstitials, and antisite defects often act as unintended dopants or compensate intentionally introduced dopants of these materials. In addition, native defects as well as contaminant impurities also limit the efficiency of light-emission in ZnSnP_2 and related materials. Thus, it is of great significance to study the nature and behaviour of such defects under different conditions.

- **Growth and realization of ferroelectric-photovoltaic effect in ZnSnS_3 thin films for solar cell and photodetector applications.**

Sponsoring Agency: SERB-DST, Govt. of India; Amount sanctioned: Rs. 24.46 lakh. Duration: 26 December 2019-25 December 2022.

Ferroelectric materials with their switchable polarization by electrical field have been considered as next generation photovoltaic applications. This research proposal is mainly

directed towards the synthesis, fabrication and characterization of a theoretically predicted new photovoltaic material based on ferroelectric LN- ZnSnS₃, thin films of which will be grown on an epitaxial GaN coated silicon substrate using spray pyrolysis technique. It is shown in theoretical study that the photovoltaic property of LN-ZnSnS₃ would be enhanced owing to its optimum band gap (~1.3 eV), lower hole effective mass (0.35m₀), large intrinsic polarization (~59 μC/cm²) and high dielectric constant (10.30) compared to conventional ferroelectric materials which are beneficial for applications in solar cell and broadband photodetector devices. In this proposed project, the microstructural, optical and electrical properties of ZnSnS₃ films are to be examined confirming their composition and phases, band gap in the visible-near infrared wavelength and the ferroelectric characteristics at room temperature. The ferroelectric-photovoltaic effect for this material will be evaluated for the first time. The photosensitivity, transient response of photocurrent under constant bias with periodically exposure of visible-near infrared light (300nm-1100nm) and the current-voltage curves under illumination would be demonstrated for the fabricated LN-ZnSnS₃ thin films. Nickel metal has been chosen for ohmic contact for this material. The short-circuit photocurrent and open-circuit photovoltage are to be switched by applying a poling voltage and their dependency on the power of illuminating light would be studied in details.

OTHER COLLABORATIVE RESEARCH PROJECTS (ON GOING)

1. Metalorganic Vapor Phase Epitaxial (MOVPE) growth of Al_{0.3}Ga_{0.7}As/GaAs multi quantum wells (MQW) (in collaboration with Dr. S. Bhunia, Surface Physics & Materials Science Division, SINP, Kolkata).

Proposal: Nowadays the use of “quantum devices” based on compound semiconductors has caused a great impact on our daily life. Very high end conceptual devices based on quantum wells such as quantum cascade lasers (QCL), vertical cavity surface emitting lasers (VCSEL), quantum well infrared photodetectors (QWIP), resonant tunneling diodes (RTD) etc. have been demonstrated. The quantum wells employed in such devices need to be of high quality, and precisely controlled thickness. High quality refers to smooth interfaces, few non-intentional incorporated impurities and high photoluminescence efficiency. Such high quality QWs are also

important in realizing two-dimensional electron gases and studying physical phenomena associated with them. In this project work, we will study MOVPE growth of GaAs/Al_{1-x}Ga_xAs QWs and study the effect of interface roughness on their optical emission properties.

2. Temperature dependent dielectric properties and ac conductivity relaxation in NiO.V₂O₅ - PEDOT nanocomposites (in collaboration with Dr. U.C. Ghosh, Former Associate Professor, Department of Chemistry, Presidency University).

Proposal: Triclinic nickel vanadium mixed oxide (NiO.V₂O₅) with particle size 80-120 nm will be synthesized via combined sol-gel-incineration method. This mixed oxide will be reinforced into the polyethylene dioxythiophene (PEDOT) matrix and characterized using x-ray diffraction (XRD), high resolution transmission electron microscopy (HRTEM), Fourier transform infrared spectroscopy (FTIR) and temperature dependent dielectric constant and ac conductivity measurements. The role of thermally activated polarons with different activation energies on the electrical conduction in the PEDOT - NiO.V₂O₅ nanocomposite will be investigated.

3. Preparation, characterization and dielectric, ac conductivity with electrochemical behavior of strontium zirconate (in collaboration with Dr. U. C. Ghosh, Former Associate Professor, Department of Chemistry, Presidency University).

4. Microstructural, electrical relaxation and magnetic characteristics of GdFeO₃-SmFeO₃ mixed improper multiferroic materials (for MSc project).

5. (A) Effect of disorder on the optical response of NiPt and Ni₃Pt alloys & (B) Band-gap tuning and optical response of two-dimensional Si_xC_{1-x}: A first-principles real-space study of disordered two-dimensional materials (in collaboration with Prof. Abhijit Mookerjee, Professor Emeritus, S.N. Bose National Center for Basic Sciences, Kolkata).

Proposal: In this theoretical and computational studies, we proposed a detailed study of the effect of chemical disorder on

the optical response of $\text{Ni}_{1-x}\text{Pt}_x$ ($0.1 < x < 0.75$) and $\text{Ni}_{3(1-x)/3}\text{Pt}_x$ ($0.1 < x < 0.3$). We shall propose a formalism which will combine a Kubo-Green hood approach with a DFT based tight-binding linear muffin-tin orbitals (TB-LMTO) basis and augmented space recursion (ASR) technique to explicitly incorporate the effect of disorder. We will examine that the chemical disorder has a large impact on optical response of Ni-Pt systems. This same approach will be used to quantitatively analyze the effect of chemical disorder on $\text{Si}_x\text{C}_{1-x}$ beyond the usual Dirac-cone approximation.

6. Development of KBiFe_2O_5 film for visible light absorbing multiferroic and photovoltaic material: Influence of confining narrow band gap nanoparticles (for Major Research & MSC project).

Proposal: This research proposal is mainly directed towards the fabrication and characterization of photovoltaic material and device based on the thin polycrystalline films of multiferroic KBiFe_2O_5 (KBFO) whose photovoltaic properties are less studied and understood. Unlike a conventional p-n junction solar cell, the photovoltaic effects in the multiferroic material (like KBFO) is relied on the internal electric field mainly responsible for the separation of photo-generated electron-hole pairs and thereby allows photovoltage higher than the optical bang gap of such materials. KBFO films will be deposited on Indium Tin Oxide coated glass and crystalline silicon substrates using spin coating technique with subsequent heat treatment for proper nucleation. Microstructural information will be obtained from X-ray diffraction and transmission electron microscopic studies. On the other hand, optical spectroscopic measurements will be undertaken to determine the absorption coefficient and band gap of the as-grown KBFO films.

In this proposed project, we are mainly interested to study the enhancement of photocurrent and spectral response of the $\text{Al-KBiFe}_2\text{O}_5\text{-Al}$ structure by embedding narrow band gap (1.2 – 1.3eV) oxide based nano-sized semiconductors (CuO , Ag_2O) in the middle of the KBiFe_2O_5 layer. The fabricated structure not only absorbs more light from visible spectrum for electron-hole pair production but also help to separate them by forming local p-n heterojunction and lowering the possibility of screening the electric charge carriers. This noble structure with embedding small gap materials is expected to generate more photocurrent with compare to the bare KBiFe_2O_5 (KBFO) single layer. The KBiFe_2O_5 (KBFO) film and source material $\text{CuO}/\text{Ag}_2\text{O}$ for embedding layer will be prepared from the nitrate/hydroxide of

their constituent elements by chemical routes. Thermal or electron beam evaporation technique to be utilized for growth of embedding layer (CuO/Ag₂O) and necessary electrodes (rectangular or disk shaped) for electrical measurements.

UNDERGRADUATE & POST GRADUATE PROJECTS SUPERVISED

1. Growth, Structural and Electrical Characterization of Zinc Tin Phosphide Thin Films for Solar Cell Applications ([Kiyafa Sultana, MSc, 2013](#)).
2. Growth and Optical Characterization of Zinc Tin Phosphide Thin Films for Solar Cell Applications ([Santanu Adikary, MSc, 2013](#)).
3. Synthesis and microstructural Behaviour of Doped Bismuth Titanate (Bi₄Ti₃O₁₂) as Nano Multiferroic Materials ([Arinda Ghosh, MSc, 2014](#)).
4. Magnetic and Electrical Characterization of Doped Bismuth Titanate (Bi₄Ti₃O₁₂) Nano Multiferroic Materials ([Sourav Kumar Maji, MSc, 2014](#)).
5. ZnO-Nanorods based Dye Sensitized Solar Cells: Preparation and Implementation ([Sucharita Saha, MSc, 2015](#)).
6. Metal Organic Vapour Phase Epitaxial Growth of (Al_yGa_{1-y})_zIn_{1-z}P/(Al_xGa_{1-x})_zIn_{1-z}P Quantum Wells and Study the Effect of Interface Roughness and Alloy Disorder on its Light Emission Properties ([Chandralina Patra, MSc, 2015](#)).
7. X-ray reflectivity analysis of semiconductor multilayer: structural and morphological characterization ([Kaustav Dutta, MSc, 2016](#)).
8. Solving Poisson Equation using FFT: Numerical Solutions of Electrostatic Potentials ([Swadhiti Majhi, BSc, 2016](#)).
9. Study of Equilibrium State of Matter using Molecular Dynamics and Calculation of Thermal Conductivity ([Kanaya Malakar, BSc, 2016](#)).
10. Study of Brownian Motion under Asymmetric Periodic Potential Well ([Unmesh Ghorai, BSc, 2017](#)).
11. Electric and Magnetic Properties of Cr Doped GdFeO₃ Multiferroic Perovskite ([Mainur Rahaman, MSc, 2017](#)).
12. Realization of Topological Darkness in Nanostructured Plasmonic Materials ([Sonali Saha, BSc, 2018](#)).
13. Photovoltaic Effect in Multiferroic KBiFe₂O₅ ([Pradip Singha Roy, MSc, 2018](#)).

14. Visible Photodetectors Based on KBiFe_2O_5 Thin Films (Kabirul Hassan, MSc, 2019).
15. Theoretical understanding and experimental realization of MSnS_3 ($M = \text{Zn, Mg}$) for photovoltaic and ferroelectric applications (DebopriyaRajak, MSc, 2023).

NOW TEACHING (UNDER GRADUATE & POST GRADUATE)

- **PHYS0191**: Mathematical Methods-1 (UG, Odd Semester)
- **PHYS0401**: Mathematical Methods-2 (UG, Odd Semester)
- **PHYS0301**: Electromagnetism 1 (UG, Odd Semester)
- **PHYS0491**: Physics Laboratory-3 (UG, Even Semester)
- **PHYS06C13**: Solid State Physics (UG, Even Semester)
- **PHYS0803**: Solid State Physics 2 (PG, Even Semester)
- **PHYS0902**: Condensed Matter Physics-2 (PG, Odd Semester)
- **PHYS0904**: Advanced Condensed Matter Physics-II (PG, Odd Semester)
- **PHYS0991**: Electronic Materials and Devices (PG, Odd Semester)
- **PHYS0904**: Physics of Nanostructured Materials (PG, Odd Semester)
- **PHYS0992**: MSc Advanced Laboratory (PG, Odd Semester)

CREATION OF RESEARCH FACILITY AND INFRASTRUCTURE DEVELOPMENT

- DST FIST Program: I am always being actively involved for planning and procuring valuable equipment to the Department for creating infrastructure facilities. Many valuable instruments like UV-Vis-NIR spectrophotometer with reflectance measurement facility (Perkin Elmer, Lamda-750), Vacuum coating unit (Hind High vacuum Co Ltd.), FTIR spectrometer (Spectrum 2, Perkin Elmer), Electrochemical Workstation (CH Instruments) etc. have been successfully installed in the Department.
- I have taken a leading part for the creation of substantial instrumental facilities for research and teaching. A new generation sophisticated XRD (PANalytical X'PERT PRO) machine was commissioned and installed in the year 2010 under my direct supervision. This equipment was purchased

from the development grant (2009-10) received from the Govt. of West Bengal.

- One HIOKI 3532-50 LCR HiTester has also been purchased from the UGC grant under my suggestions.

MAJOR DEPARTMENTAL COMMITTEES MEMBERS

- DST-FIST Program Monitoring Committee
- Purchase Committee
- Departmental Academic & PhD Committee

MAJOR UNIVERSITY COMMITTEES MEMBER & CHAIRPERSONS

2013-2019	Purchase-Cum Tender Committees
2016-2019	Chairman, University Admission Committee
2016-2019	Member, Finance Committee
2016-2019	Member, Governing Body, Presidency University
2016-2022	Member, University Doctorate Committee (Sciences)
2016-2022	Member, Faculty Council (Sciences)

(Arabinda Nayak)